

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:)	
)	Examiner:
Kazutoshi Kojima et al.)	
)	Group Art Unit:
Application No.:)	
)	
Corresponding International Filing No.:)	
PCT/JP2004/011894)	
)	
Filed: Herewith)	
)	
For: SILICON CARBIDE EPITAXIAL)	
WAFER, METHOD FOR)	
PRODUCING SUCH WAFER,)	
AND SEMICONDUCTOR)	
DEVICE FORMED ON SUCH)	
WAFER)	

Mail Stop PCT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SECOND PRELIMINARY AMENDMENT

Sir:

Please amend the above-identified patent application as follows.

Amendments to the Specification begin on page two of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page four of this paper.

Remarks begin on page six of this paper.